

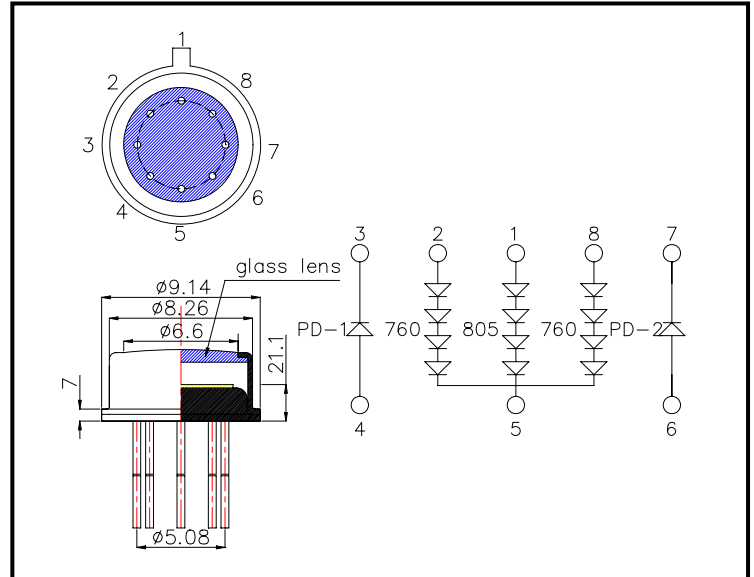
L4*760/4*805/4*850/PD2*006-40Q96-I multi-wavelength LED

◆ Outer dimension (Unit: mm)

L4*760/4*805/4*850/PD2*006-40Q96-I consists of 12chips of AlGaAs (760nm, 805nm and 850nm) LED and 2chips of Si-PD mounted with AlN heat sink pedestal on TO-5 stem and sealed with a flat glass can.

◆ Specifications

- | | |
|-------------------------|--|
| 1) Product Name | Multi-wavelength LED |
| 2) Type No. | L4*765/4*805/4*850/
PD2*006-40Q96-I |
| 3) Chip | |
| (1) Chip material (LED) | AlGaAs, Si |
| (2) Peak wavelength | 760, 805, 850nm |
| (3) Chip numbers (LED) | Each 4pcs |
| 4) Package | |
| (1) Stem | TO-5, 8pins type |
| (2) Lens | Flat glass can |



◆ Absolute Maximum Ratings [Ta=25°C]

Item	Symbol	Maximum Rated Value				Unit
		760	805	850	PD	
Power Dissipation	PD	720	680	640		mW
Forward Current	IF	75	100	100		mA
Pulse Forward Current	IF	200	300	500		mA
Reverse Voltage	VR	5			100	V
Operating Temperature	TOPR	-20 ~ +80				°C
Storage Temperature	TSTG	-30 ~ +100				°C
Soldering Temperature	TSOL	240				°C

‡Soldering condition: Soldering condition must be completed within 3 seconds at 240°C and is allowed in the area apart 3mm from the bottom of the lamp.

◆ Electro-Optical Characteristics [Ta=25°C]

Symbol	Wavelength	Condition	Minimum	Typical	Maximum	Unit
VF	760	IF=50mA		7.4	8.0	V
	805					
	850					
IR		VR=10V			10	uA
PO	760	IF=50mA	15	30		mW
	805		18	30		
	850		20	30		
λP	760	IF=50mA	745	760	775	nm
	805		790	805	820	
	850		835	850	865	
Δλ	760	IF=50mA		40		nm
	805			40		
	850			40		
PD/IL	760	VR=10V		60		uA
	805			80		
	850			80		
PD/ID	-	VR=10V			50	nA

‡Total Radiated Power is measured by Photodyne #500